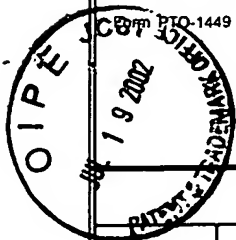
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		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.		
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U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>[Signature]</i>	AA	5,972,800	10/99	Hasegawa				
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							Yes No	
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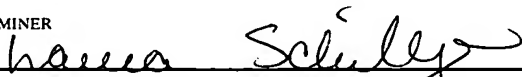
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	Document Number	Date	Country	Class	Subclass	Translation	
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	AR		Liu, C.T. et al., "Multiple Gate Oxide Thickness for 2GHz System-on-a-Chip Technologies", IEEE 1998, pp. 589-592.
	AS		
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<i>SL</i>	AR		Ko, L. et al., "The Effect of Nitrogen Incorporation into the Gate Oxide By Using Shallow Implantation of Nitrogen and Drive-In Process", IEEE 1996, pp. 32-35.
<i>SL</i>	AS		Doyle, B. et al., "Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS Processing", IEEE Vol. 16 (7), July 1995, pp. 301-302.
<i>SL</i>	AT		Kuroi, T. et al., "The Effects of Nitrogen Implantation Into P+Poly-Silicon Gate on Gate Oxide Properties", 1994 Sympos. on VLSI Technology Digest of Technical Papers, IEEE 1994, pp. 107-108.

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